

**PRODUCTION OF DIELECTRIC INSULATED AND ISOLATED SUBSTRATE**

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- european:
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Abstract of JP53057978

PURPOSE: To increase the scale of integration while increasing the area of island regions by performing bonding and firing of glass powder buried in isolating grooves in the same process in a dielectric insulated and isolated substrate which mutually electrically insulates and isolates a multiplicity of single crystal island regions formed with IC elements and continuously supports and fixed these.

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TITLE: Prod'n. of dielectric insulation isolation substrate -
with monocrystalline island of increased area and
improved integration density

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Basic Abstract Text - ABTX (2):

The improvement comprises making isolating grooves a monocrystalline silicon substrate; filling the grooves with a glass compsn. powder through a silicon oxide film; placing a support body having an adhesive layer on the silicon substrate such that the adhesive layer is in contact with the groove-formed silicon substrate surface; heating to convert the glass powder into glass and adhesively bond the silicon substrate and the support body; and then removing the silicon substrate from the back surface to form buried silicon islands.

